

10/553245

J009 Rec'd PCT/PTO 17 OCT 2005

Sheet 1 of 3

Form PTO-1449 (REV. 8-83)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO.  NREL 01-43	SERIAL NO. Not Yet Assigned
<b>INFORMATION DISCLOSURE CITATION</b>  <i>(Use several sheets if necessary)</i> <b>METHOD FOR PRODUCING HIGH CARRIER CONCENTRATION P-TYPE TRANSPARENT CONDUCTING OXIDES</b>		APPLICANT Li et al.	EXAMINER Not Yet Assigned
		FILING DATE	GROUP Not Yet Assigned

## U. S. PATENT DOCUMENTS

Examiner INITIAL	REF	DOCUMENT NUMBER	DATE	NAME			FILING DATE IF APPROPRIATE
		4,612,411	09/16/86	Wieting	136	265	
		5,078,803	01/17/92	Pier et al.	136	256	
		5,324,365	06/28/94	Niwa	136	256	
		5,420,043	05/30/95	Niwa	438	96	
		5,458,753	10/17/95	Sato et al.	204	192.29	
		5,578,501	11/26/96	Niwa	438	96	
		5,604,133	02/18/97	Aoike	438	96	
		5,612,229	03/18/97	Yoshida	438	72	
		5,620,924	04/15/97	Takizawa	427	108	

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER		DATE CONSIDERED
<p><b>*EXAMINER:</b> Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>		

10/553245

JC09 Rec'd PCT/PTO 17 OCT 2009

Sheet 2 of 3

Form PTO-1449 (REV. 8-83)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO.  NREL 01-43	SERIAL NO. Not Yet Assigned
<b>INFORMATION DISCLOSURE CITATION</b>  <i>(Use several sheets if necessary)</i> <b>METHOD FOR PRODUCING HIGH CARRIER CONCENTRATION P-TYPE TRANSPARENT CONDUCTING OXIDES</b>		APPLICANT Li et al.	EXAMINER Not Yet Assigned
		FILING DATE	GROUP Not Yet Assigned

## U. S. PATENT DOCUMENTS

Examiner INITIAL	REF	DOCUMENT NUMBER	DATE	NAME			FILING DATE IF APPROPRIATE
		5,716,480	02/10/98	Matsuyama et al.	136	249	
		5,804,466	09/08/98	Arao et al.	438	95	
		5,913,986	06/22/99	Matsuyama	136	255	
		5,990,416	11/23/99	Windisch et al.	136	255	
		6,040,521	03/21/00	Kushiya et al.	136	265	
		6,043,427	03/28/00	Nishimoto	136	258	
		6,107,116	08/22/00	Kariya et al.	438	87	
		6,187,150 B1	02/13/01	Yoshimi et al.	204	192.29	
		6,238,808	05/29/01	Arao et al.	428	629	
		6,424,687B1	06/15/01	Schropp	136	255	

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED	
<b>*EXAMINER:</b> Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		

Sheet 3 of 3

Form PTO-1449 (REV. 8-83)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. NREL 01-43	SERIAL NO. Not Yet Assigned
<b>INFORMATION DISCLOSURE CITATION</b>  (Use several sheets if necessary) <b>METHOD FOR PRODUCING HIGH CARRIER CONCENTRATION P-TYPE TRANSPARENT CONDUCTING OXIDES</b>		APPLICANT Li et al.	EXAMINER Not Yet Assigned
		FILING DATE	GROUP Not Yet Assigned

## U. S. PATENT DOCUMENTS

Examiner INITIAL	REF	DOCUMENT NUMBER	DATE	NAME			FILING DATE IF APPROPRIATE
		5,756,207	05/26/1998	Clough et al.			

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	AA	M. Joseph et al., "p-type Electrical Conduction in ZnO Thin films by Ga and N Codoping," Jpn. J. Appl. Phys. 38, (1999) pp. L1205-1207
	AB	K. Minegishi et al., "Growth of p-type Zinc oxide Films by Chemical Vapor Deposition," Jpn. J. Appl. Phys. 36, (1997) pp. L1453-L145
	AC	X. Gao et al., "Pulsed Reactive Laser Deposition of p-type ZnO Film Enhanced by an Electron Cyclotron Resonance Source," J. of Crystal Growth, 223 (2001) 135-139
	AD	S. B. Zhang et al. J. Appl. Phys. 83, 3192 (1998).
	AE	Y. Sato et al., Thin Solid Films 281-282, 445 (1996)
	AF	Yan et al. in "Control of Doping by impurity Chemical Potentials: Predictions for p-Type ZnO," Physical Review Letters 86, 5723 (2001)